



www.vishay.com

Vishay Semiconductors

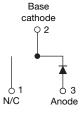
HEXFRED®, **Ultrafast Soft Recovery Diode, 15 A**

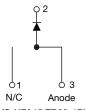




TO-263AB (D²PAK)

TO-262AA





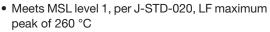
VS-HFA15 TB60SPbF

VS-HFA15 TB60-1PbF

PRODUCT SUMMARY	
Package	TO-263AB (D ² PAK), TO-262AA
I _{F(AV)}	15 A
V_{R}	600 V
V _F at I _F	1.2 V
t _{rr} (typ.)	23 ns
T _J max.	150 °C
Diode variation	Single die

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RBM} and Q_{rr}





AEC-Q101 qualified

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





RoHS

HALOGEN FREE

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA15TB60SPbF, VS-HFA15TB60-1PbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A continuous current, the VS-HFA15TB60SPbF, VS-HFA15TB60-1PbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA15TB60SPbF, VS-HFA15TB60-1PbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V _R		600	V			
Maximum continuous forward current	I _F	T _C = 100 °C	15				
Single pulse forward current	I _{FSM}		150	Α			
Maximum repetitive forward current	I _{FRM}		60				
Maximum namer dissination	Б	T _C = 25 °C	74	W			
Maximum power dissipation	P_{D}	T _C = 100 °C	29	VV			
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C			



Vishay Semiconductors

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-	
Maximum forward voltage		I _F = 15 A		-	1.3	1.7	V
	V_{FM}	I _F = 30 A	See fig. 1	-	1.5	2.0	
		I _F = 15 A, T _J = 125 °C		-	1.2	1.6	
Maximum reverse		V _R = V _R rated	See fig. 2	-	1.0	10	
leakage current	I _{RM}	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See lig. 2	-	400	1000	μA
Junction capacitance	C _T	V _R = 200 V	See fig. 3	-	25	50	pF
Series inductance	L _S	Measured lead to lead 5 mm from page 1	ackage body	-	8.0	-	nH

DYNAMIC RECOVERY	CHARACT	TERISTICS (T _J = 25	°C unless otherwise	specifie	d)		
PARAMETER	SYMBOL	TEST CON	NDITIONS	MIN.	TYP.	MAX.	UNITS
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	Vμs, V _R = 30 V	-	23	-	
Reverse recovery time See fig. 5	t _{rr1}	T _J = 25 °C		-	50	60	ns
occ lig. o	t _{rr2}	T _J = 125 °C		-	105	120	
Peak recovery current	I _{RRM1}	T _J = 25 °C	I _F = 15 A dI _F /dt = 200 A/μs	-	4.5	6.0	A nC
See fig. 6	I _{RRM2}	T _J = 125 °C		-	6.5	10	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	84	180	
See fig. 7	Q _{rr2}	T _J = 125 °C	V _R = 200 V	-	241	600	IIC
Peak rate of fall of recovery	dI _{(rec)M} /dt1	T _J = 25 °C		-	188	-	- A/μs
current during t _b See fig. 8	dI _{(rec)M} /dt2	T _J = 125 °C		-	160	-	Αν μο

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R _{thJC}		-	-	1.7		
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-		
Weight			-	2.0	-	g	
vveigni			-	0.07	-	oz.	
		Case style D ² PAK		HFA15	15TB60S		
Marking device		Case style TO-262		HFA15TB60-1			





www.vishay.com

Vishay Semiconductors

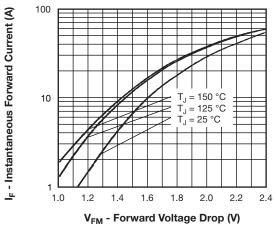


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

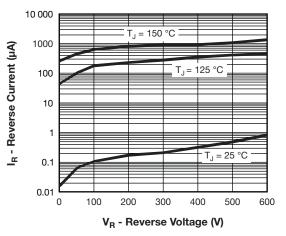


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

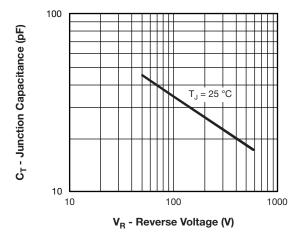


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

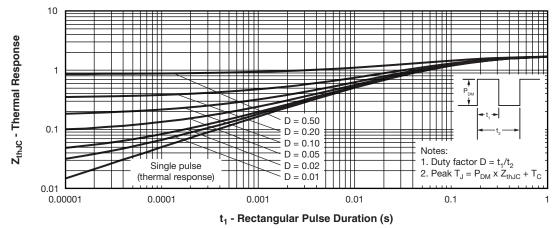


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



www.vishay.com

Vishay Semiconductors

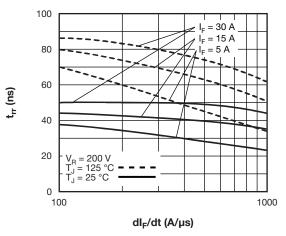


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

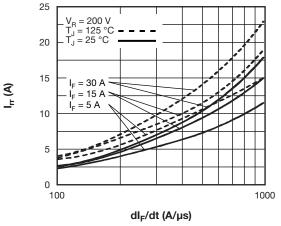


Fig. 6 - Typical Recovery Current vs. dl_F/dt

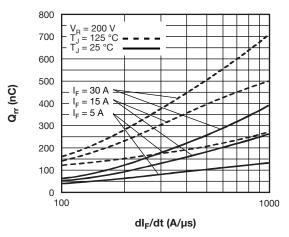


Fig. 7 - Typical Stored Charge vs. dl_F/dt

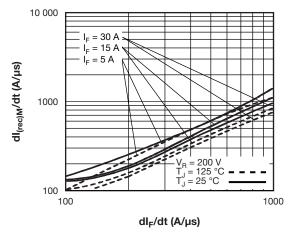


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

Vishay Semiconductors

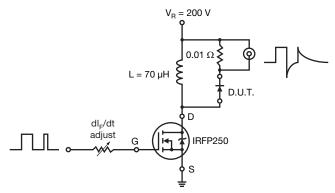
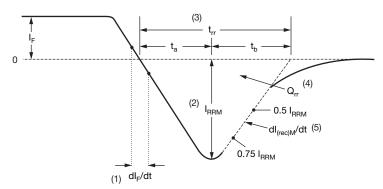


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_{F}$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and $\mathbf{I}_{\mathrm{RRM}}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

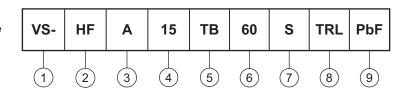
(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

- HEXFRED® family

Electron irradiated

- Current rating (15 = 15 A)

- Package: TB = TO-220

6 - Voltage rating (60 = 600 V)

7 - • S = D²PAK

- • -1 = TO-262

None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D2PAK package)

• TRR = tape and reel (right oriented, for D²PAK package)

9 - • PbF = lead (Pb)-free, for tube packaged

• P = lead (Pb)-free, for tape and reel packaged

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER TUBE OR TAPE AND REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-HFA15TB60SPBF	50	1000	Antistatic plastic tube					
VS-HFA15TB60STRLP	800	800	13" diameter reel					
VS-HFA15TB60STRRP	800	800	13" diameter reel					
VS-HFA15TB60-1PBF	50	1000	Antistatic plastic tube					

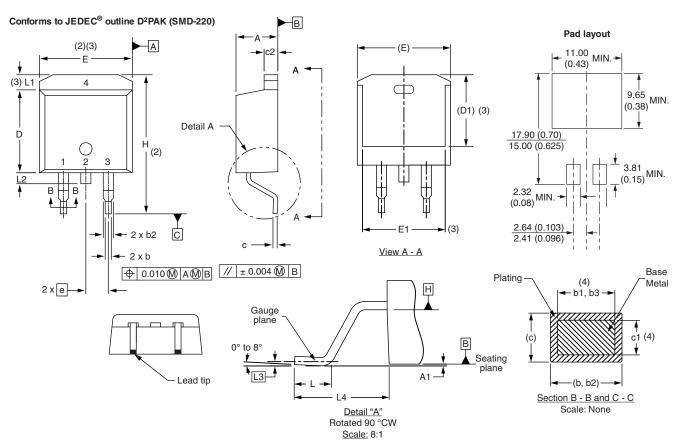
LINKS TO RELATED DOCUMENTS					
Dimensions	TO-263AB (D ² PAK): <u>www.vishay.com/doc?95046</u>				
Differisions	TO-262AA: www.vishay.com/doc?95419				
Part marking information	TO-263AB (D ² PAK): www.vishay.com/doc?95054				
Part marking information	TO-262AA: www.vishay.com/doc?95420				
Packaging information	www.vishay.com/doc?95032				
SPICE model	www.vishay.com/doc?95357				



Vishay Semiconductors

D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES SYMBOL	MILLIM	ETERS	INC	HES	NOTES		
STWBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010) BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

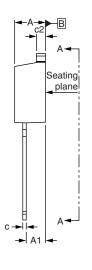
- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB

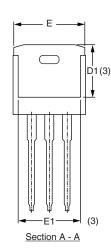


Vishay Semiconductors

TO-262

DIMENSIONS in millimeters and inches



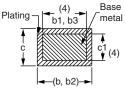


♦0.010**M**A**M**B

Lead assignments



<u>Diodes</u>
1. - Anode (two die)/open (one die)
2., 4. - Cathode
3. - Anode



Section B - B and C - C Scale: None

CVMPOL	MILLIN	METERS	INCH	INCHES			
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		
А	4.06	4.83	0.160	0.190			
A1	2.03	3.02	0.080	0.119			
b	0.51	0.99	0.020	0.039			
b1	0.51	0.89	0.020	0.035	4		
b2	1.14	1.78	0.045	0.070			
b3	1.14	1.73	0.045	0.068	4		
С	0.38	0.74	0.015	0.029			
c1	0.38	0.58	0.015	0.023	4		
c2	1.14	1.65	0.045	0.065			
D	8.51	9.65	0.335	0.380	2		
D1	6.86	8.00	0.270	0.315	3		
Е	9.65	10.67	0.380	0.420	2, 3		
E1	7.90	8.80	0.311	0.346	3		
е	2.54	BSC	0.100	BSC			
L	13.46	14.10	0.530	0.555			
L1	-	1.65	-	0.065	3		
L2	3.56	3.71	0.140	0.146			

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}\,\,$ Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.